







SN74AXC1T45-Q1 SCES901D - FEBRUARY 2019 - REVISED JANUARY 2024

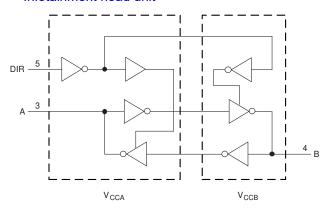
# SN74AXC1T45-Q1 Automotive Qualified Single-Bit Dual-Supply Bus Transceiver with Configurable Voltage Translation, Tri-State Outputs

#### 1 Features

- AEC-Q100 qualified for automotive applications
- Fully configurable dual-rail design allows each port to operate with a power supply range from 0.65V to 3.6V
- Operating temperature: -40°C to +125°C
- Glitch-free power supply sequencing
- Maximum quiescent current ( $I_{CCA} + I_{CCB}$ ) of  $10\mu A$ (85°C maximum) and 16µA (125°C maximum)
- Up to 500Mbps support when translating from 1.8 to 3.3V
- V<sub>CC</sub> isolation feature
  - If Either V<sub>CC</sub> input is below 100mV, all I/O outputs are disabled and become highimpedance
- I<sub>off</sub> supports partial-power-down mode operation
- Latch-up performance exceeds 100mA per JESD 78. Class II
- ESD protection exceeds JESD 22:
  - 8000-V Human body model
  - 1000-V Charged-device model

# 2 Applications

- ADAS fusion
- ADAS front camera
- HEV battery management system
- Infotainment head unit



**Functional Block Diagram** 

# 3 Description

The SN74AXC1T45-Q1 is AEC-Q100 qualified singlebit non-inverting bus transceiver that uses two individually configurable power-supply rails. The device is operational with both  $V_{\text{CCA}}$  and  $V_{\text{CCB}}$ supplies as low as 0.65V. The A port is designed to track V<sub>CCA</sub>, which accepts any supply voltage from 0.65V to 3.6V. The B port is designed to track V<sub>CCB</sub>, which also accepts any supply voltage from 0.65V to 3.6V. Additionally, the SN74AXC1T45-Q1 is compatible with a single-supply system.

The DIR pin determines the direction of signal propagation. With the DIR pin configured HIGH, translation is from Port A to Port B. With DIR configured LOW, translation is from Port B to Port A. The DIR pin is referenced to V<sub>CCA</sub>, meaning that its logic-high and logic-low thresholds track with V<sub>CCA</sub>.

This device is fully specified for partial-power-down applications using the Ioff current. The Ioff protection circuitry is designed so that no excessive current is drawn from or to an input, output, or combined I/O that is biased to a specific voltage while the device is powered down.

The V<sub>CC</sub> isolation feature is designed so that if either V<sub>CCA</sub> or V<sub>CCB</sub> is less than 100mV, both I/O ports enter a high-impedance state by disabling their outputs.

Glitch-free power supply sequencing allows either supply rail to be powered on or off in any order while providing robust power sequencing performance.

#### **Package Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE(2)
SN74AXC1T45-Q1	DCK (SC70, 6)	2mm × 2.1mm
3N/4AXC1143-Q1	DRY (SON, 6)	1.45mm × 1mm

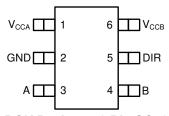
- For more information, see Section 11
- The package size (length × width) is a nominal value and includes pins, where applicable.



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# **4 Pin Configuration and Functions**



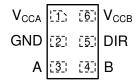


Figure 4-2. DRY Package, 6-Pin SON Transparent (Top View)

Figure 4-1. DCK Package, 6-Pin SC70 (Top View)

**Table 4-1. Pin Functions** 

F	PIN		DESCRIPTION	
NAME	NO.	TYPE <sup>(1)</sup>	DESCRIPTION	
V <sub>CCA</sub>	1	_	A-port supply voltage. 0.65V ≤ V <sub>CCA</sub> ≤ 3.6V	
GND	2	_	Ground	
A	3	I/O	Input/output A. This pin is referenced to V <sub>CCA</sub> .	
В	4	I/O	Input/output B. This pin is referenced to V <sub>CCB</sub> .	
DIR	5	I	Direction control signal. See Device Functional Modes for functionality	
V <sub>CCB</sub>	6	_	B-port supply voltage. $0.65V \le V_{CCB} \le 3.6V$ .	

(1) I = input, O = output



# **5 Specifications**

# 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
$V_{CCA}$	Supply voltage A		-0.5	4.2	V
V <sub>CCB</sub>	Supply voltage B		-0.5	4.2	V
		I/O Ports (A Port)	-0.5	4.2	
$V_{I}$	Input Voltage <sup>(2)</sup>	I/O Ports (B Port)	-0.5	4.2	V
		Control Inputs	-0.5	4.2	
V	Valle and a multi-district the bight incomed and a support of state (2)	A Port	-0.5	4.2	.,
Vo	Voltage applied to any output in the high-impedance or power-off state <sup>(2)</sup>	B Port	-0.5	4.2	V
.,	(2) (2)	A Port	-0.5 V <sub>CCA</sub>		V
Vo	Voltage applied to any output in the high or low state <sup>(2) (3)</sup>	B Port	-0.5	V <sub>CCB</sub> + 0.2	\ \ \
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0	-50		mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> < 0	-50		mA
Io	Continuous output current	-	-50	50	mA
	Continuous current through V <sub>CC</sub> or GND	-100	100	mA	
TJ	Junction Temperature			150	°C
T <sub>STG</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- (2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The output positive-voltage rating may be exceeded up to 4.2V maximum if the output current rating is observed.

## 5.2 ESD Ratings

			VALUE	UNIT
	Human body model (HBM), per AEC Q100-002 <sup>(1)</sup>	±8000	V	
V <sub>(ESD)</sub>	Liectiostatic discharge	Charged device model (CDM), per AEC Q100-011	±1000	V

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.



# **5.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2) (3)

·		<u> </u>	,	MIN	MAX	UNIT
V <sub>CCA</sub>	Supply voltage A			0.65	3.6	V
V <sub>CCB</sub>	Supply voltage B			0.65	3.6	V
			V <sub>CCI</sub> = 0.65V - 0.75V	V <sub>CCI</sub> x 0.70		
			V <sub>CCI</sub> = 0.76V - 1 V	V <sub>CCI</sub> x 0.70		
		Data Inputs	V <sub>CCI</sub> = 1.1 V - 1.95V	V <sub>CCI</sub> x 0.65		
			V <sub>CCI</sub> = 2.3V - 2.7V	1.6		
.,	Link lavalinavkvaltava		V <sub>CCI</sub> = 3V - 3.6V	2		V
$V_{IH}$	High-level input voltage		V <sub>CCA</sub> = 0.65V - 0.75V	V <sub>CCA</sub> x 0.70		V
			V <sub>CCA</sub> = 0.76V - 1 V	V <sub>CCA</sub> x 0.70		
		Control Input (DIR) Referenced to V <sub>CCA</sub>	V <sub>CCA</sub> = 1.1 V - 1.95V	V <sub>CCA</sub> x 0.65		
		Tronordiod to VCCA	V <sub>CCA</sub> = 2.3V - 2.7V	1.6		
			V <sub>CCA</sub> = 3V - 3.6V	2		
			V <sub>CCI</sub> = 0.65V - 0.75V		V <sub>CCI</sub> x 0.30	
			V <sub>CCI</sub> = 0.76V - 1 V		V <sub>CCI</sub> x 0.30	
			V <sub>CCI</sub> = 1.1 V - 1.95V		V <sub>CCI</sub> x 0.35	
			V <sub>CCI</sub> = 2.3V - 2.7V		0.7	
\/	Low lovel input veltage		V <sub>CCI</sub> = 3V - 3.6V		0.8	V
$V_{IL}$	Low-level input voltage		V <sub>CCA</sub> = 0.65V - 0.75V		V <sub>CCA</sub> x 0.30	V
			V <sub>CCA</sub> = 0.76V - 1 V		V <sub>CCA</sub> x 0.30	
		Control Input (DIR) Referenced to V <sub>CCA</sub>	V <sub>CCA</sub> = 1.1 V - 1.95V		V <sub>CCA</sub> x 0.35	
		Tronoronous to VCCA	V <sub>CCA</sub> = 2.3V - 2.7V		0.7	
			V <sub>CCA</sub> = 3V - 3.6V		0.8	
VI	Input voltage (3)			0	3.6	V
\/ -	Output voltage	Active State		0	V <sub>CCO</sub>	V
Vo	Output voltage	Tri-State		0	3.6	_ v
Δt/Δν	Input transition rate				100	ns/V
T <sub>A</sub>	Operating free-air tempe	rature		-40	125	°C

<sup>(1)</sup> VCCI is the VCC associated with the input port.

# **5.4 Thermal Information**

		SN74AXC1T45-Q1			
	THERMAL METRIC(1)	DCK (SC70)	DRY (SON)	UNIT	
		6 PINS	6 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	235.3	305.2	°C/W	
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	160.5	202.2	°C/W	
$R_{\theta JB}$	Junction-to-board thermal resistance	76.9	181.1	°C/W	
ΨЈТ	Junction-to-top characterization parameter	59.7	41.9	°C/W	
ΨЈВ	Junction-to-board characterization parameter	77.1	180.0	°C/W	

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

Product Folder Links: SN74AXC1T45-Q1

<sup>(2)</sup> VCCO is the VCC associated with the output port.

<sup>3)</sup> All unused inputs of the device must be held at VCC or GND for proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs.



# **5.5 Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted) (1) (2)

						Operating free-air temperature (T <sub>A</sub> )							
PA	RAMETER	TEST CONDITIONS		V <sub>CCA</sub> V <sub>CCB</sub>	-40°C to 85°C -40°C to 125°C					UNI			
						MIN T	YP <sup>(3)</sup> M	AX MIN	TYP	MAX	•		
			I <sub>OH</sub> = -100μA	0.7V - 3.6V	0.7V - 3.6V	V <sub>CCO</sub> – 0.1		V <sub>CCO</sub> – 0.1					
			I <sub>OH</sub> = -50μA	0.65V	0.65V	0.55		0.55					
			I <sub>OH</sub> = -200μA	0.76V	0.76V	0.58		0.58					
	High-level		I <sub>OH</sub> = -500μA	0.85V	0.85V	0.65		0.65					
$V_{OH}$	output voltage	$V_I = V_{IH}$	I <sub>OH</sub> = -3mA	1.1V	1.1V	0.85		0.85	,		V		
			I <sub>OH</sub> = -6mA	1.4V	1.4V	1.05	,	1.05					
			I <sub>OH</sub> = -8mA	1.65V	1.65V	1.2		1.2					
			I <sub>OH</sub> = -9mA	2.3V	2.3V	1.75		1.75					
			I <sub>OH</sub> = -12mA	3V	3V	2.3		2.3					
			I <sub>OL</sub> = 100μA	0.7V - 3.6V	0.7V - 3.6V		(	0.1		0.1			
			I <sub>OL</sub> = 50μA	0.65V	0.65V		(	0.1		0.1			
			I <sub>OL</sub> = 200μA	0.76V	0.76V		0.	18		0.18			
			I <sub>OL</sub> = 500μA	0.85V	0.85V		(	0.2		0.2			
$V_{OL}$	Low-level output voltage	$V_I = V_{IL}$	I <sub>OL</sub> = 3mA	1.1V	1.1V		0.	25		0.25			
	output voltage		I <sub>OL</sub> = 6mA	1.4V	1.4V		0.	35		0.35			
			I <sub>OL</sub> = 8mA	1.65V	1.65V		0.	45		0.45			
			I <sub>OL</sub> = 9mA	2.3V	2.3V		0.	55		0.55			
			I <sub>OL</sub> = 12mA	3V	3V		(	).7		0.7			
		Control inp	out (DIR): V <sub>I</sub> =	0.65V- 3.6V	0.65V- 3.6V	-1		1 –1.5	-	1.5			
I <sub>I</sub>	current	A or B Por GND	t: Vi = V <sub>CCI</sub> or	0.65V- 3.6V	0.65V- 3.6V	-4		4 -8		8	μA		
	Partial power	A or B Por	A or B Por		t: Vi or Vo = 0V -	0V	0V - 3.6V	-5		5 –7.5		7.5	
l <sub>off</sub>	down current	3.6V		0V - 3.6V	0V	-5		5 –7.5		7.5	μA		
				0.65V- 3.6V	0.65V- 3.6V			8		12			
$I_{CCA}$	V <sub>CCA</sub> supply current	V <sub>I</sub> = V <sub>CCI</sub> or GND	I <sub>O</sub> = 0	0V	3.6V	-2		-8			μΑ		
	Garroni	or orto		3.6V	0V			2		8			
				0.65V- 3.6V	0.65V- 3.6V			8		12			
I <sub>CCB</sub>	V <sub>CCB</sub> supply current	V <sub>I</sub> = V <sub>CCI</sub> or GND	I <sub>O</sub> = 0	0V	3.6V			2		8	μΑ		
	Carrent	OI OI D		3.6V	0V	-2		-8					
I <sub>CCA</sub> +	Combined supply current	V <sub>I</sub> = V <sub>CCI</sub> or GND	I <sub>O</sub> = 0	0.65V- 3.6V	0.65V- 3.6V			10		16	μA		
Cı	Control input capacitance	V <sub>I</sub> = 3.3V c	or GND	3.3V	3.3V		4.4		4.4		pF		
C <sub>IO</sub>	Data I/O capacitance, A Port	V <sub>O</sub> = 1.65\ dBm sine \	/ DC +1MHz -16 wave	3.3V	0V		5		5		pF		
C <sub>IO</sub>	Data I/O capacitance, B Port	V <sub>O</sub> = 1.65\ dBm sine \	/ DC +1MHz -16 wave	0V	3.3V		5		5		pF		

<sup>(1)</sup> (2) VCCI is the VCC associated with the input port.

VCCO is the VCC associated with the output port.

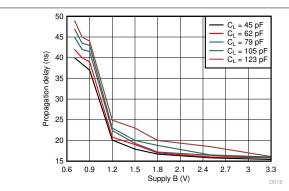
All typical data is taken at 25°C.



# 5.6 Operating Characteristics: $T_A = 25^{\circ}C$

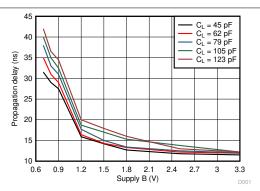
	PARAMETER	TEST CONDITIONS	V <sub>CCA</sub>	V <sub>CCB</sub>	MIN TYP	MAX	UNIT
			0.7V	0.7V	1.3		
			0.8V	V8.0	1.3		
			0.9V	0.9V	1.3		
	Power Dissipation Capacitance	C <sub>L</sub> = 0, R <sub>L</sub> = Open f =	1.2V	1.2V	1.3		
	per transceiver (A to B)	1MHz, $t_r = t_f = 1 \text{ ns}$	1.5V	1.5V	1.3		pF
			1.8V	1.8V	1.4		
			2.5V	2.5V	1.7		
			3.3V	3.3V	2.1		
C <sub>pdA</sub>			0.7V	0.7V	9.2		
			0.8V	V8.0	9.4		
			0.9V	0.9V	9.4		
	Power Dissipation Capacitance	C <sub>L</sub> = 0, R <sub>L</sub> = Open f =	1.2V	1.2V	9.8		nE
	per transceiver (B to A)	1MHz, t <sub>r</sub> = t <sub>f</sub> = 1 ns	1.5V	1.5V	10.1		pF
			1.8V	1.8V	11.0		
			2.5V	2.5V	14.4		
			3.3V	3.3V	18.6		
		C <sub>L</sub> = 0, R <sub>L</sub> = Open f =	0.7V	0.7V	9.2		
			0.8V	V8.0	9.3		
			0.9V	0.9V	9.4		
	Power Dissipation Capacitance		1.2V	1.2V	9.7		pF
	per transceiver (A to B)	1MHz, $t_r = t_f = 1 \text{ ns}$	1.5V	1.5V	10.1		þr
			1.8V	1.8V	11.0		
			2.5V	2.5V	14.4		
			3.3V	3.3V	18.3		
C <sub>pdB</sub>			0.7V	0.7V	1.3		
			0.8V	V8.0	1.3		
			0.9V	0.9V	1.3		
	Power Dissipation Capacitance	C <sub>L</sub> = 0, R <sub>L</sub> = Open f =	1.2V	1.2V	1.3		nE
	per transceiver (B to A)	1MHz, $t_r = t_f = 1 \text{ ns}$	1.5V	1.5V	1.3		pF
			1.8V	1.8V	1.4		
			2.5V	2.5V	1.7		
			3.3V	3.3V	2.1		

### 5.7 Typical Characteristics



 $T_A = 25^{\circ}C$   $V_{CCA} = 0.7V$ 

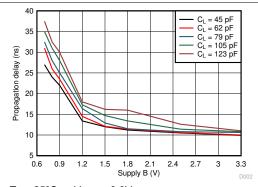
Figure 5-1. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance



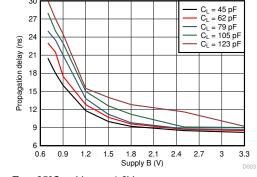
 $T_A = 25^{\circ}C$  $V_{CCA} = 0.8V$ 

30

Figure 5-2. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance



 $T_A = 25^{\circ}C$  $V_{CCA} = 0.9V$ 



 $T_A = 25$ °C  $V_{CCA} = 1.2V$ 



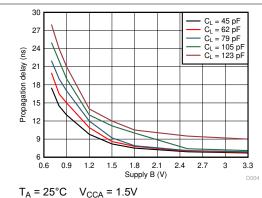


Figure 5-5. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance

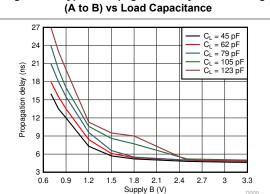


Figure 5-4. Typical Propagation Delay of Low-to-High

 $T_A = 25$ °C  $V_{CCA} = 1.8V$ 

Figure 5-6. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance



# 5.7 Typical Characteristics (continued)

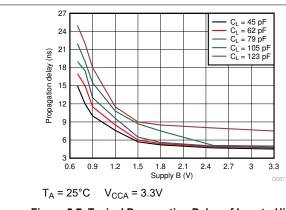
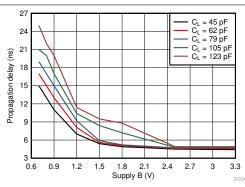
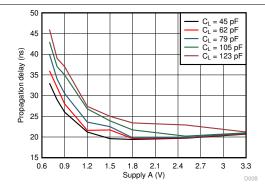


Figure 5-7. Typical Propagation Delay of Low-to-High

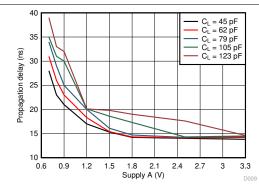


 $T_A = 25^{\circ}C$  $V_{CCA} = 2.5V$ 

Figure 5-8. Typical Propagation Delay of Low-to-High (A to B) vs Load Capacitance (A to B) vs Load Capacitance

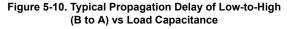


 $T_A = 25$ °C  $V_{CCA} = 0.7V$ 



 $T_A = 25^{\circ}C$   $V_{CCA} = 0.8V$ 





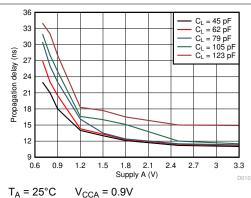
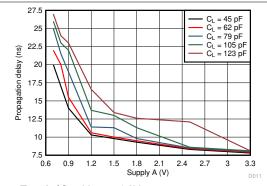


Figure 5-11. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance



 $T_A = 25$ °C  $V_{CCA} = 1.2V$ 

Figure 5-12. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance

# 5.7 Typical Characteristics (continued)

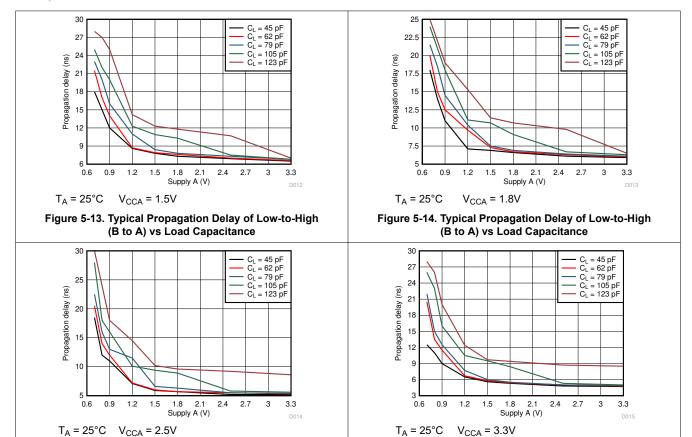


Figure 5-15. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance

Figure 5-16. Typical Propagation Delay of Low-to-High (B to A) vs Load Capacitance

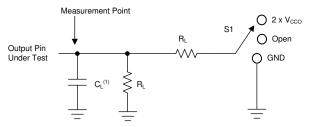


### **6 Parameter Measurement Information**

# 6.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- f = 1MHz
- $Z_O = 50\Omega$
- dv/dt ≤ 1 ns/V

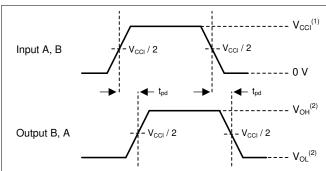


A. C<sub>L</sub> includes probe and jig capacitance.

Figure 6-1. Load Circuit

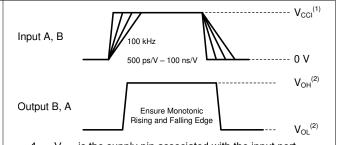
**Table 6-1. Load Circuit Conditions** 

	Parameter	V <sub>cco</sub>	R <sub>L</sub>	CL	S <sub>1</sub>	V <sub>TP</sub>
Δt/Δν	Input transition rise or fall rate	0.65V - 3.6V	1ΜΩ	15pF	Open	N/A
	Propagation (delay) time	1.1 V – 3.6V	2kΩ	15pF	Open	N/A
t <sub>pd</sub>	Propagation (delay) time	0.65V - 0.95V	20kΩ	15pF	Open	N/A
		3V – 3.6V	2kΩ	15pF	2 × V <sub>CCO</sub>	0.3V
+ +	t <sub>en</sub> , t <sub>dis</sub> Enable time, disable time	1.65V – 2.7V	2kΩ	15pF	2 × V <sub>CCO</sub>	0.15V
ten, tdis	chable time, disable time	1.1 V – 1.6V	2kΩ	15pF	2 × V <sub>CCO</sub>	0.1V
		0.65V - 0.95V	20kΩ	15pF	2 × V <sub>CCO</sub>	0.1V
		3V – 3.6V	2kΩ	15pF	GND	0.3V
	Enable time, disable time	1.65V – 2.7V	2kΩ	15pF	GND	0.15V
<sup>l</sup> en, <sup>l</sup> dis	Enable time, disable time	1.1 V – 1.6V	2kΩ	15pF	GND	0.1V
		0.65V - 0.95V	20kΩ	15pF	GND	0.1V



- 1. V<sub>CCI</sub> is the supply pin associated with the input port.
- V<sub>OH</sub> and V<sub>OL</sub> are typical output voltage levels that occur with specified R<sub>L</sub>, C<sub>L</sub>, and S<sub>1</sub>

Figure 6-2. Propagation Delay



- 1.  $V_{CCI}$  is the supply pin associated with the input port.
- 2.  $V_{OH}$  and  $V_{OL}$  are typical output voltage levels that occur with specified  $R_L$ ,  $C_L$ , and  $S_1$

Figure 6-3. Input Transition Rise or Fall Rate

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DIR V<sub>CCA</sub> / 2 Output A(2) V<sub>CCO</sub> / 2  $V_{OL} + V_{TP}$  $t_{dis}$ V<sub>OH</sub> - V<sub>TP</sub> Output A<sup>(3)</sup> Output B(2) <sub>cco</sub> / 2  $V_{OL} + V_{TP}$ t<sub>dis</sub>- $V_{OH}$  -  $V_{TP}$ V<sub>CCO</sub> / 2 Output B(3) ----- GND

- 1. Illustrative purposes only. Enable Time is a calculation as described in the data sheet.
- 2. Output waveform on the condition that input is driven to a valid Logic Low.
- 3. Output waveform on the condition that input is driven to a valid Logic High.
- 4. V<sub>CCI</sub> is the supply pin associated with the input port
- 5. V<sub>CCO</sub> is the supply pin associated with the output port.
- 6.  $V_{OH}$  and  $V_{OL}$  are typical output voltage levels that occur with specified  $R_L$ ,  $C_L$ , and  $S_1$

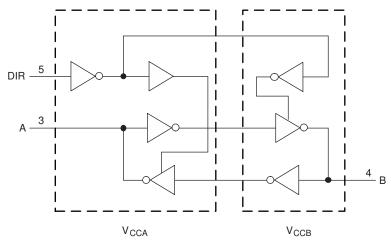
Figure 6-4. Disable and Enable Time

# 7 Detailed Description

#### 7.1 Overview

The SN74AXC1T45-Q1 is AEC-Q100 qualified single-bit, dual-supply, non-inverting voltage level translator. Pin A and the direction control pin are referenced to  $V_{CCA}$  logic levels and pin B is referenced to  $V_{CCB}$  logic levels, as depicted in the *Functional Block Diagram*. The A port can accept I/O voltages ranging from 0.65V to 3.6V, and the B port can accept I/O voltages from 0.65V to 3.6V. A logic high on the DIR pin enables data transmission from A to B and a logic low on the DIR pin enables data transmission from B to A.

#### 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law  $(R = V \div I)$ .

Signals applied to the inputs need to have fast edge rates, as defined by  $\Delta t/\Delta v$  in *Recommended Operating Conditions* to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the standard CMOS input.

#### 7.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

#### 7.3.3 Partial Power Down (I<sub>off</sub>)

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. The maximum leakage into or out of any input or output pin on the device is specified by I<sub>off</sub> in the *Electrical Characteristics*.

### 7.3.4 V<sub>CC</sub> Isolation

The inputs and outputs for this device enter a high-impedance state when either supply is <100mV.

#### 7.3.5 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage so long as they remain below the maximum input voltage value specified in the *Recommended Operating Conditions*.

Product Folder Links: SN74AXC1T45-Q1

### 7.3.6 Negative Clamping Diodes

The inputs and outputs to this device have negative clamping diodes as depicted in Figure 7-1.

#### **CAUTION**

Voltages beyond the values specified in the Absolute Maximum Ratings table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

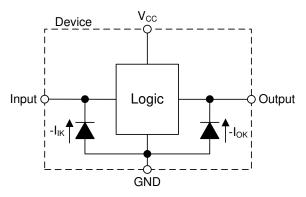


Figure 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

#### 7.3.7 Fully Configurable Dual-Rail Design

Both the  $V_{CCA}$  and  $V_{CCB}$  pins can be supplied at any voltage from 0.65V to 3.6V, making the device suitable for translating between any of the voltage nodes (0.7V, 0.8V, 0.9V, 1.2V, 1.8V, 2.5V and 3.3V).

#### 7.3.8 I/Os with Integrated Static Pull-Down Resistors

To help avoid floating inputs on the I/Os, this device has  $288k\Omega$  typical integrated weak pull-downs on all data I/Os. This feature allows all inputs to be left floating without the concern for unstable outputs or increased current consumption. This also helps to reduce external component count for applications where not all channels are used or need to be fixed low. If an external pull-up is required, it should be no larger than  $30k\Omega$  to avoid contention with the  $288k\Omega$  internal pull-down.

#### 7.3.9 Supports High-Speed Translation

The SN74AXC1T45-Q1 device can support high data-rate applications. The translated signal data rate can be up to 500Mbps when the signal is translated from 1.8V to 3.3V.

#### 7.4 Device Functional Modes

Table 7-1 lists the device functions for the DIR input.

**Table 7-1. Function Table** 

INPUT <sup>(1)</sup> DIR	OPERATION
L	B data to A bus
н	A data to B bus

(1) Input circuits of the data I/Os always are active.

# 8 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### 8.1 Application Information

The SN74AXC1T45-Q1 device can be used in level-translation applications for interfacing devices or systems with one another when they are operating at different interface voltages. The maximum data rate can be up to 500Mbps when the device translate signals from 1.8V to 3.3V.

#### 8.1.1 Enable Times

Calculate the enable times for the SN74AXC1T45-Q1 using the following formulas:

$$t_{PZH}$$
 (DIR to A) =  $t_{PLZ}$  (DIR to B) +  $t_{PLH}$  (B to A) (1)

$$t_{PZL}$$
 (DIR to A) =  $t_{PHZ}$  (DIR to B) +  $t_{PHL}$  (B to A) (2)

$$t_{PZH}$$
 (DIR to B) =  $t_{PLZ}$  (DIR to A) +  $t_{PLH}$  (A to B) (3)

$$t_{PZL} (DIR to B) = t_{PHZ} (DIR to A) + t_{PHL} (A to B)$$
(4)

In a bidirectional application, these enable times provide the maximum delay time from the time the DIR bit is switched until an output is expected. For example, if the SN74AXC1T45-Q1 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay.

#### 8.2 Typical Applications

#### 8.2.1 Interrupt Request Application

Figure 8-1 shows an example of the SN74AXC1T45-Q1 being used in an application where a system controller flags an interrupt request (IRQ) to the CPU. The system controller determines the direction of the IRQ line to either flag an interrupt to the CPU or allow the CPU to drive data on the line. In this application the controller is operating at 3.3V while the CPU can operate as low as 0.65V.

The SN74AXC1T45-Q1 device is used to allow these devices to communicate at the appropriate voltage levels. Because the SN74AXC1T45-Q1 does not have an output-enable  $(\overline{OE})$  pin, the system designer should take precautions to avoid bus contention between the CPU and controller when changing directions.

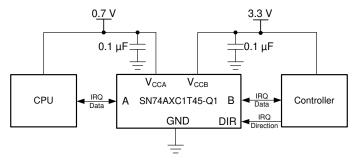


Figure 8-1. Interrupt Request Application

Product Folder Links: SN74AXC1T45-Q1

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# 8.2.1.1 Design Requirements

For this design example, use the parameters listed in Table 8-1.

**Table 8-1. Design Parameters** 

DESIGN PARAMETERS	EXAMPLE VALUES
Input voltage range	0.65V to 3.6V
Output voltage range	0.65V to 3.6V

#### 8.2.1.2 Detailed Design Procedure

To begin the design process, determine the following:

- · Input voltage range
  - Use the supply voltage of the device that is driving the SN74AXC1T45-Q1 device to determine the input voltage range. For a valid logic-high, the value must exceed the high-level input voltage (V<sub>IH</sub>) of the input port. For a valid logic low the value must be less than the low-level input voltage (V<sub>IL</sub>) of the input port.
- Output voltage range
  - Use the supply voltage of the device that the SN74AXC1T45-Q1 device is driving to determine the output voltage range.

### 8.2.1.3 Application Curve



Figure 8-2. Up Translation at 2.5MHz (0.7V to 3.3V)

### 8.2.2 Universal Asynchronous Receiver-Transmitter (UART) Interface Application

Figure 8-3 shows the SN74AXC1T45-Q1 being used for the two-bit UART interface application. One SN74AXC1T45-Q1 device is used to level shift the voltage and drive the TX from the processor to the GPS Module while a second SN74AXC1T45-Q1 device is used to drive the TX Data line from the GPS Module to the Processor.

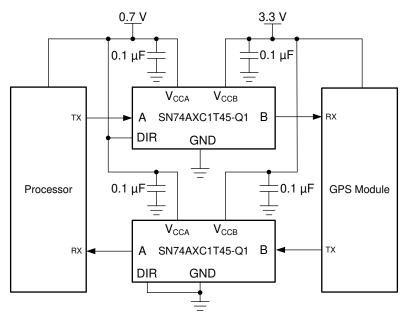


Figure 8-3. UART Interface Application

## 8.2.2.1 Design Requirements

Refer to Section 8.2.1.1.

#### 8.2.2.2 Detailed Design Procedure

Refer to Section 8.2.1.2.

#### 8.3 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

This device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices. For more information regarding the power up glitch performance of the AXC family of level translators, see the *Power Sequencing for AXC Family of Devices* application report

### 8.4 Layout

## 8.4.1 Layout Guidelines

For device reliability, following common printed-circuit board layout guidelines are recommended:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible.
- Use short trace lengths to avoid excessive loading.

### 8.4.2 Layout Example



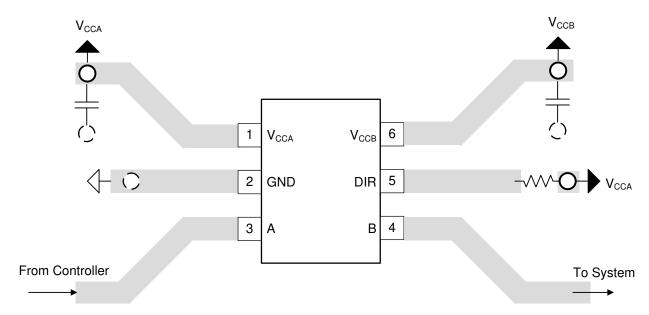


Figure 8-4. PCB Layout Example



# 9 Device and Documentation Support

## 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, Evaluate SN74AXC1T45DRL Using a Generic EVM application report
- Texas Instruments, Implications of Slow or Floating CMOS Inputs application report
- Texas Instruments, Power Sequencing for the AXC Family of Devices application report

### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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# 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (January 2020) to Revision D (January 2024)     Added the I/Os with Integrated Static Pull-Down Resistors section	Page
Changes from Revision B (September 2019) to Revision C (January 2020)	Page
Device with DRY package is now Active status	2
Updated I <sub>CCA</sub> , I <sub>CCB</sub> , and I <sub>CCA</sub> + I <sub>CCB</sub> to reflect updated performance of device	5
Ohanna fara Barisian A (Inha 2040) ta Barisian B (Oantambar 2040)	Page
Changes from Revision A (July 2019) to Revision B (September 2019)	

Product Folder Links: SN74AXC1T45-Q1

 ww	. 4:	~~	-

С	hanges from Revision * (February 2019) to Revision A (July 2019)	Page
•	Added DRY package to Device Information table	1
•	Added DRY package to Pin Configurations	2
	Added DRY package to Section 5.4 table	
	, •	

# 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 23-May-2025

#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
SN74AXC1T45QDCKRQ1	Active	Production	SC70 (DCK)   6	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1E1
SN74AXC1T45QDCKRQ1.B	Active	Production	SC70 (DCK)   6	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1E1
SN74AXC1T45QDRYRQ1	Active	Production	SON (DRY)   6	5000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	G2
SN74AXC1T45QDRYRQ1.B	Active	Production	SON (DRY)   6	5000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	G2

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN74AXC1T45-Q1:

<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE OPTION ADDENDUM**

www.ti.com 23-May-2025

• Catalog : SN74AXC1T45

NOTE: Qualified Version Definitions:

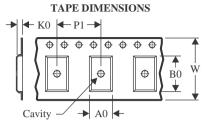
• Catalog - TI's standard catalog product

# **PACKAGE MATERIALS INFORMATION**

www.ti.com 30-Oct-2023

### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

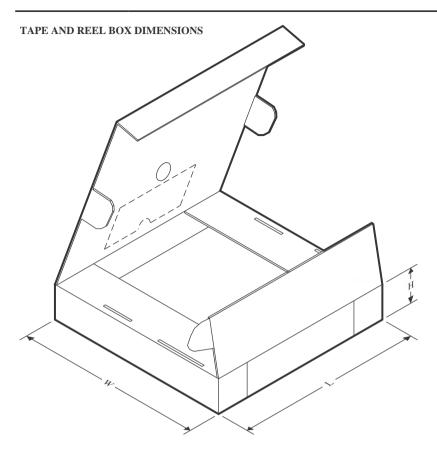
#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AXC1T45QDCKRQ1	SC70	DCK	6	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74AXC1T45QDRYRQ1	SON	DRY	6	5000	180.0	9.5	1.2	1.65	0.7	4.0	8.0	Q1

www.ti.com 30-Oct-2023

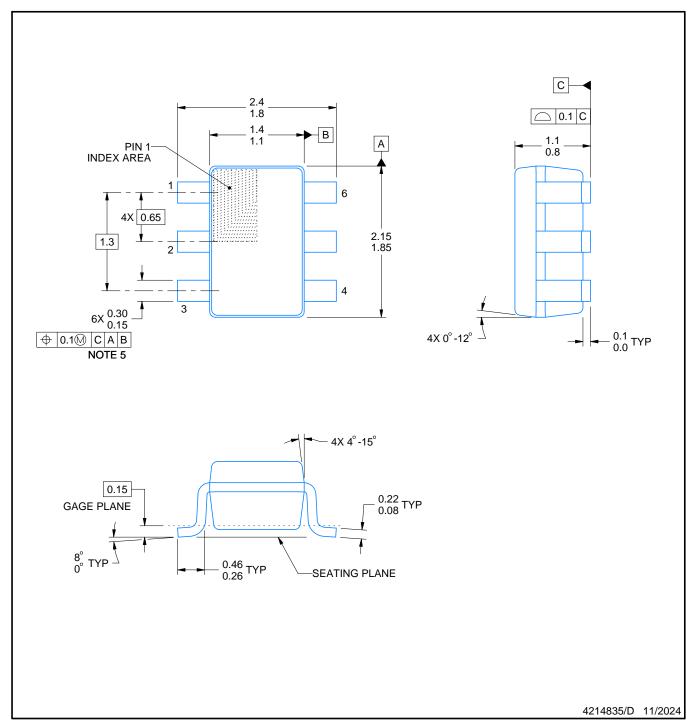


## \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AXC1T45QDCKRQ1	SC70	DCK	6	3000	190.0	190.0	30.0
SN74AXC1T45QDRYRQ1	SON	DRY	6	5000	189.0	185.0	36.0



SMALL OUTLINE TRANSISTOR



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

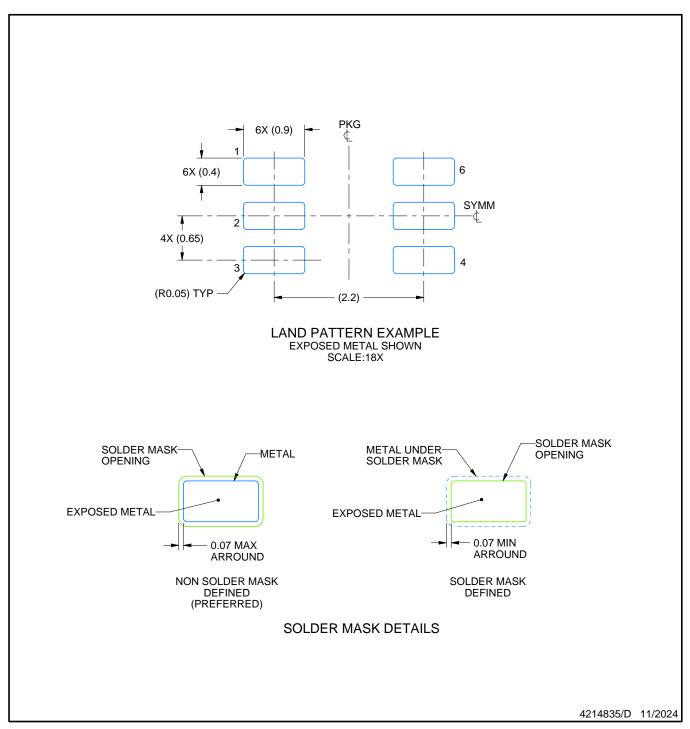
  2. This drawing is subject to change without notice.

  3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.

  4. Falls within JEDEC MO-203 variation AB.



SMALL OUTLINE TRANSISTOR



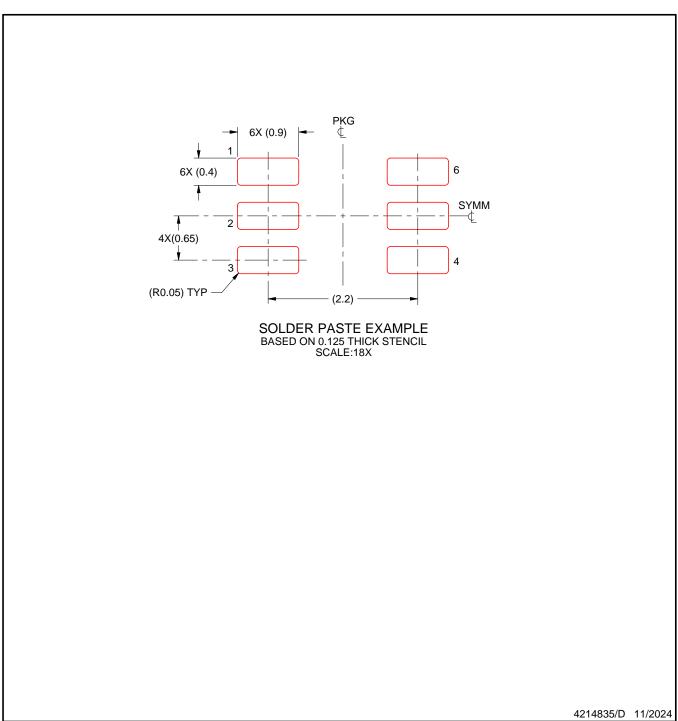
NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.





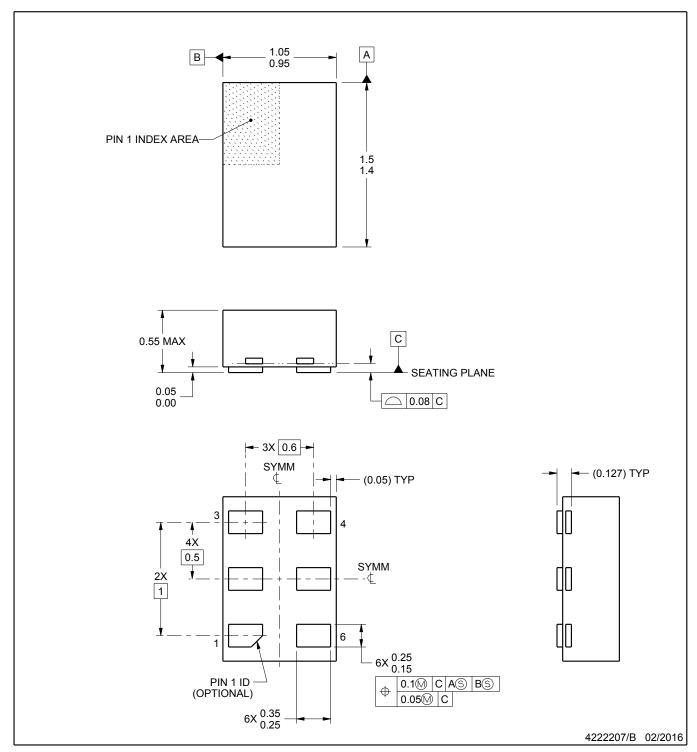
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







PLASTIC SMALL OUTLINE - NO LEAD



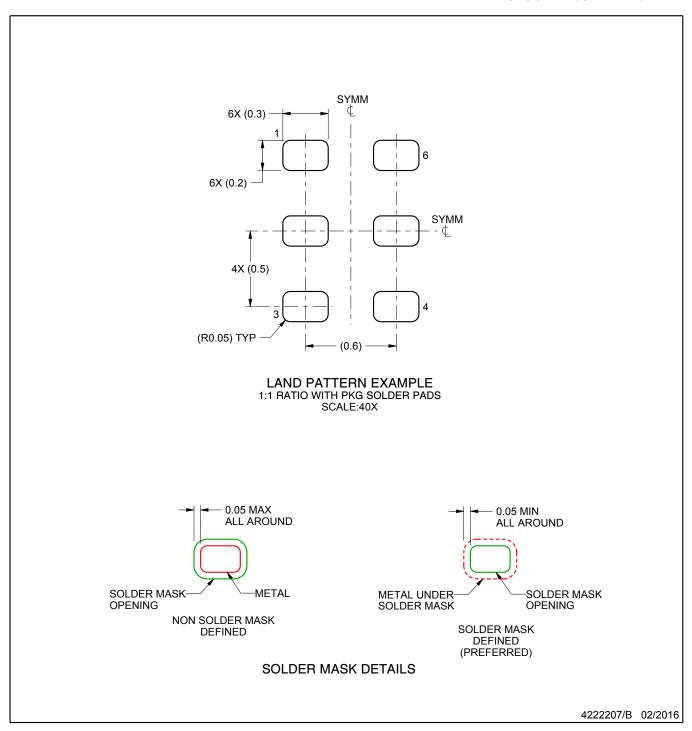
#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.



PLASTIC SMALL OUTLINE - NO LEAD

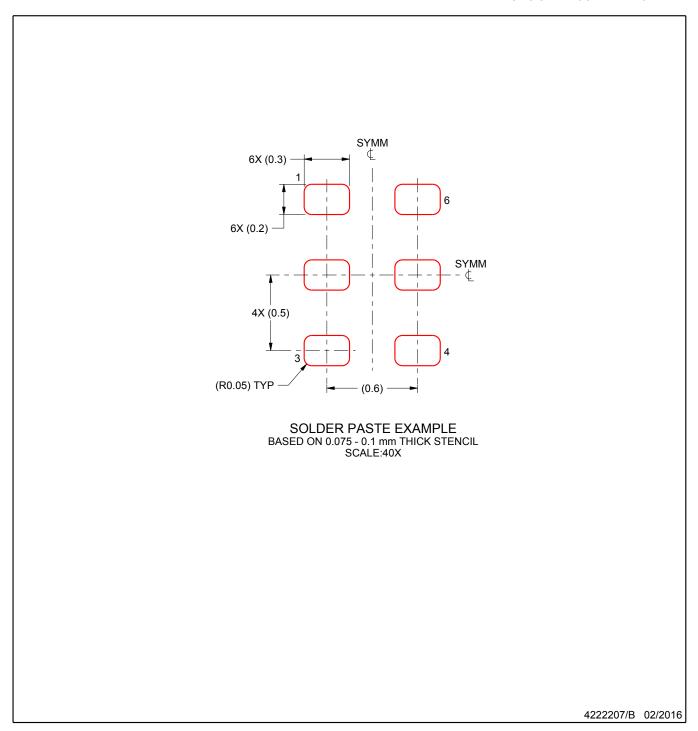


NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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